

STRUCTURE OF A DEEP TRENCH-TYPE DRAM AND METHOD FOR MAKING
THE SAME

ABSTRACT

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A structure and a manufacture method of a DRAM device with deep trench capacitors are described. Each capacitor has a collar oxide layer with different height for electrical isolation and leakage reduction. Further, the DRAM device has strip-type active areas to improve some optical errors and thus reduce sufficiently the contact 10 resistance of a buried strap film of a capacitor.

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